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High-efficiency red electrophosphorescence devices

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We demonstrate high-efficiency red electrophosphorescent organic light-emitting devices employing bis(2-(2'-benzo[4,5-a]thienyl)) pyridinato-N,C^{3'}) iridium(acetylacetonate) [Btp₂Ir(acac)] as a red phosphor. A maximum external quantum efficiency of $\eta_{\rm ext}=(7.0\pm0.5)\%$ and power efficiency of $\eta_p=(4.6\pm0.5)$ lm/W are achieved at a current density of J=0.01 mA/cm². At a higher current density of J=100 mA/cm², $\eta_{\rm ext}=(2.5\pm0.3)\%$ and $\eta_p=(0.56\pm0.05)$ lm/W are obtained. The electroluminescent spectrum has a maximum at a wavelength of $\lambda_{\rm max}=616$ nm with additional intensity peaks at $\lambda_{\rm sub}=670$ and 745 nm. The Commission Internationale de L'Eclairage coordinates of (x=0.68, y=0.32) are close to meeting video display standards. The short phosphorescence lifetime ($\sim 4~\mu s$) of Btp₂Ir(acac) leads to a significant improvement in $\eta_{\rm ext}$ at high currents as compared to the previously reported red phosphor, 2,3,7,8,12,13,17,18-octaethyl-12H, 23H-prophine platinum (II) PtOEP with a lifetime of $\sim 50~\mu s$. © 2001 American Institute of Physics. [DOI: 10.1063/1.1355007]

Heavy-metal complexes, 1,2 where strong spin-orbit coupling leads to singlet-triplet state mixing, can result in highefficiency electrophosphorescence in organic light-emitting devices (OLEDs).³⁻⁶ For example, OLEDs employing the phosphor, factris(2-phenylpyridine)iridium [Ir(ppy)₃], exhibit green emission with an external quantum efficiency $(\eta_{\rm ext})$ of ~15%.⁶ By designing appropriate ligands for heavy-metal complexes, high-efficiency electrophosphorescence at other emission colors is anticipated for highperformance full-color display applications. Both redemitting fluorescent and phosphorescent dopants have shown promise for use in OLEDs. While fluorescent dyes, including 4-dicyanomethylene-2-methyl-6-[2-(2,3,6,7-tetra-hydro-1H, 5H-benzo[ij]quinolizin-8-yl)-4H-pyran (DCM2)^{8,9} and porphyrin derivatives (TPP, ¹⁰ ZnTPP, ¹¹ and TPC¹²), have been investigated, their maximum external quantum efficiencies are limited to less than 1%. Furthermore, the red phosphocomplexes $(EuL_3)^{13,14}$ europium 2,3,7,8,12,13,17,18-octaethyl-12H,23H-porphine platinum (II) (PtOEP) have been studied.^{3,4} Although EuL₃ complexes show very strong red Eu3+ ion emission (with an internal quantum efficiency $\eta_{int} > 80\%$), ¹⁵ the long lifetime of the Eu³⁺ excited state (\sim 350 μ s) results in pronounced triplet– triplet (T-T) annihilation at high current.¹⁴ In addition, the high triplet energy of the ligands causes backward energy transfer to the host molecule, leading to $\eta_{\rm ext}$ < 1.4%. ¹⁴ The highest $\eta_{\text{ext}} = 5.6\%$ for a red phosphor has been achieved with PtOEP doped into 4,4'-N,N'-dicarbazole-biphenyl.

In this study, we demonstrate red organometallic phosphors characterized by a high quantum efficiency and a short radiative lifetime. 17 The metal complexes contain cyclometalated benzothienylpyridine ligands, i.e., $bis(2-(2'-benzo[4,5-\alpha]thienyl)$ pyridinato-N,C^{3'}) iridium (acetyl-acetonate) $[btp_2Ir(acac)]^7$ and (2-(2'-benzo)[4, $5-\alpha$ [thienyl) pyridinato-N,C³') platinum (acetylacetonate) [btpt(acac)], shown in Fig. 1. The synthesis of btpPt(acac) was prepared by a method analogous to that used⁷ for btp₂Ir(acac). The small π - π * transition energy of the btp ligand relative to other ligands used in heavy-metal phosphors leads to a low-energy triplet excited state, giving strong red phosphorescence. OLEDs employing these phosphors were grown by high vacuum (10⁻⁶ Torr) thermal evaporation onto pre-cleaned glass substrates as described elsewhere. Device I is comprised of a 20 Ω/\Box indium tin oxide (ITO) anode, a 50-nm-thick 4,4'-bis[N-(1-naphthyl)-N-phenyl-amino biphenyl hole transport layer (HTL), a 20nm-thick light-emitting layer (EML) consisting of a conductive CBP host doped with \sim 7% of the guest phosphor, a 10-nm-thick 2,9-dimethyl-4,7-diphenyl-phenanthroline hole and exciton blocking layer,4 a 65-nm-thick tris(8hydroxyquinoline)aluminum (Alq₃) electron transport layer (ETL), and a cathode comprised of a 100-nm-thick (10:1) MgAg layer, with a further 20 nm Ag deposited as a protective cap (Fig. 1). Device II has the ITO anode, a 60-nm-thick 4,4'-bis[N,N'-(3-tolyl)amino]-3,3'-dimethylbiphenyl⁶ HTL, a 25-nm-thick 2,2',2"-(1,3,5-benzenetriyl)tris[1-phenyl-1H-benzimidazole] (TPBI)¹⁸ EML doped with \sim 7% phos-

⁽CBP).⁴ However, the relatively long phosphorescence lifetime ($\sim\!80~\mu s$) again results in T–T annihilation at high current.¹⁶

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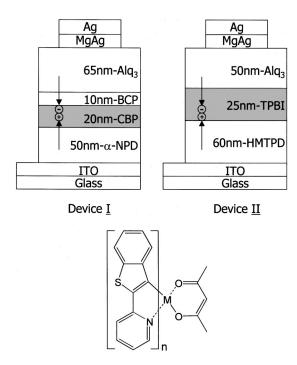


FIG. 1. Device structures \underline{I} and \underline{II} . Molecular structure of the btp₂M(acac) phosphors (here M = Ir, n = 2 and M = Pt, n = 1).

phor, a 50-nm-thick Alq_3 ETL, and the same cathode as in device I.

Figure 2 shows $\eta_{\rm ext}$ and the power efficiency (η_p) as functions of current density for device <u>I</u> with a btp₂Ir(acac) guest. A maximum $\eta_{\rm ext} = (7.0 \pm 0.5)\%$ and $\eta_p = (4.6 \pm 0.5)$ lm/W, and a luminance of 6.5 cd/m² were obtained at J = 0.1 mA/cm². The device showed a gradual decrease of $\eta_{\rm ext}$ with increasing current, which has been previously attributed to T-T annihilation. Nevertheless, at J = 100 mA/cm², the device efficiency remained high at $\eta_{\rm ext} = (2.5 \pm 0.3)\%$ and $\eta_p = (0.56 \pm 0.05)$ lm/W. A maximum luminance of 6800 cd/m² was obtained at J = 690 mA/m².

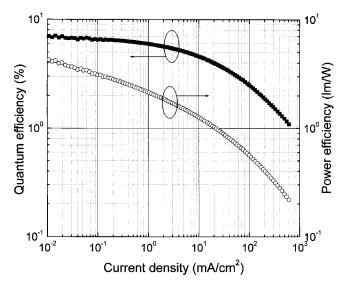


FIG. 2. External quantum efficiency (η_{ext}) and power efficiency (η_p) vs current density for device \underline{I} with a btp₂Ir(acac) guest.

Table I summarizes the electroluminescence characteristics of btp₂Ir(acac), btpPt(acac), PtOEP and Eu(TTA)₃phen (TTA = thenoyltrifluoroacetone, phen = 1, 10-phenanthroline)guests in devices \underline{I} and II. A maximum $\eta_{\text{ext}} \sim 7\%$ was obtained with btp₂Ir(acac) in both devices I and II, and PtOEP in device II. Also, the maximum η_p of btp₂Ir(acac) was (4.6 ± 0.5) lm/W which is significantly higher than that of PtOEP, since the spectral peak of the latter compound is \sim 30 nm redshifted relative to btp₂Ir(acac). A pronounced improvement in $\eta_{\rm ext}$ of btp₂Ir(acac) was observed at high current. At $J = 100 \,\mathrm{mA/cm^2}$, the btp₂Ir(acac) doped device <u>I</u> showed a relatively high $\eta_{\rm ext} = (2.5 \pm 0.5)\%$, compared with PtOEP and Eu(TTA)₃phen doped devices <u>I</u> with $\eta_{\text{ext}} = (0.61)$ ± 0.05)% and $\eta_{\rm ext} = (0.21 \pm 0.05)$ %, respectively. The roll off in $\eta_{\rm ext}$ with J is consistent with the electrophosphorescent lifetimes, τ , of the several materials employed. As shown

TABLE I. Red electrophosphorescent OLED characteristics. External quantum efficiency ($\eta_{\rm ext}$), and power efficiency ($\eta_{\rm p}$) are given as functions of current density. Peak wavelength ($\lambda_{\rm max}$) in electroluminescent spectrum. Transient electrophosphorescent time (τ) under electrical pulse excitation with pulse width of 500 ns. The characteristic current (J_0) of triplet–triplet annihilation.

$\eta_{ m ext}(\%) \ \left[\ \eta_{ m p}({ m lm/W}) ight] \ { m at} \ J({ m mA/cm^2})$										
		J = 0.01	0.1	1	10	100	1000	$\lambda_{\text{max}}(nm)$	$ au(\mu s)$	$J_0(\mathrm{mA/cm^2})$
Btp ₂ Ir(acac)	Device <u>I</u>	7.0 (4.6)	6.7 (3.1)	6.0 (2.1)	4.4 (1.3)	2.5 (0.56)	0.69 (0.16)		6.5	27.4
	Device <u>II</u>	6.9 (5.7)	6.8 (3.6)	5.9 (2.5)	3.7 (1.4)	1.6 (0.57)	0.53 (0.14)	616	4.0	11.0
BtpPt(acac)	Device <u>I</u>	2.7 (2.5)	2.7 (1.4)	2.6 (0.93)	1.9 (0.54)	1.0 (0.25)	0.37 (0.083)	-10	9.3	37.7
	Device <u>II</u>	2.2 (1.7)	2.2 (1.1)	2.1 (0.72)	1.3 (0.34)	0.57 (0.12)	0.0.2 (0.036)	610	5.6	14.5
PtOEP	Device <u>I</u>	5.2 (1.3)	5.2 (1.1)	4.1 (0.64)	2.1 (0.25)	0.67 (0.066)	0.18 (0.015)	650	86.5	6.4
	Device <u>II</u>	6.9 (1.4)	6.9 (1.0)	4.3 (0.53)	1.9 (0.17)	0.5 (0.039)	0.10 (0.010)	050	49.6	2.6
Eu(TTA) ₃ phen	Device <u>I</u>	1.4 (1.2)	1.3 (0.94)	1.2 (0.53)	0.68 (0.21)	0.21 (0.08)	•••	614	350	3.6

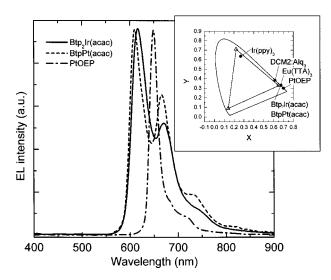


FIG. 3. Electroluminescent spectra of device $\underline{\text{II}}$ employing btp₂tr(acac), PtOEP or btpPt(acac) at a current density of $J=1.3\,\text{mA/cm}^2$. Inset: CIE coordinates for btp₂tr(acac) ($x=0.67,\ y=0.33$), btpPt(acac) ($x=0.67,\ y=0.33$), PtOEP ($x=0.70,\ y=0.30$) and Eu(TTA)₃phen ($x=0.68,\ y=0.32$) doped devices and a 2%-DCM2: Alq₃ ($x=0.61,\ y=0.39$) device. The triangles show the NTSC recommended blue, green, and red coordinates.

previously, the characteristic current (J_0) at which $\eta_{\rm ext}$ falls to 50% its peak value due to T-T annihilation is inversely proportional to $\tau^{2,14,19}$ This figure of merit of a phosphor is listed in Table I along with τ for the devices tested. The btp₂Ir(acac) lifetime is ~12 times smaller than that of PtOEP, leading to considerably improved high-current performance of the Ir-based compound. The low $\eta_{\rm ext}$ of btpPt(acac) is consistent with its low photoluminescence efficiency $[(8\pm2)\%]$ compared with that of btp₂Ir(acac) $[(21\pm5)\%]$ and PtOEP $[(40\pm10)\%]$.

The EL spectra originating from the triplet-excited states of the phosphors shown in Fig. 3 are coincident with those of the phosphors in a dilute solution. The Commission Internationale de L'Eclairage (CIE) coordinates for the four devices are compared with a fluorescent 2%-DCM2:Alq₃ device (x = 0.61,0.39) (inset of Fig. 2). Similar to the $Eu(TTA)_3$ phen of (x = 0.68, y = 0.32), the btp₂Ir(acac) and btpPt(acac) doped devices demonstrate a saturated red emission (x = 0.67, y = 0.33) which is close to the National Television Standards Committee recommended red for a video display. Furthermore, the EL spectra and CIE coordinates of btp₂Ir(acac) in devices I and II are independent of current (Fig. 4). Even at $J>100 \,\mathrm{mA/cm^2}$, blue emission from either the CBP or TPBI host is negligible, indicating complete energy transfer under the excitation conditions used: a direct consequence of the short phosphor lifetime of this compound.²⁰

In summary, we demonstrated high-efficiency, high-brightness red phosphorescent OLEDs employing benzothie-nylpyridine (btp) as a ligand in iridium and platinum complexes. Significant improvements in $\eta_{\rm ext}$ as compared with PtOEP were achieved due to the short phosphorescence lifetimes of <10 μ s of the new compounds studied, thereby minimizing T-T annihilation and saturation of the ligand excited state.

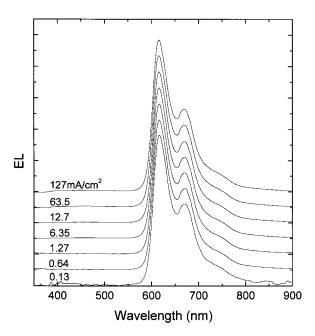


FIG. 4. Electroluminescent spectra of device \underline{II} with a $btp_2(acac)$ guest dopant as a function of OLED drive current density.

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- ¹J.-M. Lehn, *Supermolecular Chemistry* (VCH, Weinheim, Germany, 1995).
- ²C. A. Bignozzi, J. R. Schoonover, and F. Scandola, Prog. Inorg. Chem. 44, 1 (1997).
- ³M. A. Baldo, D. F. O'Brien, Y. You, A. Shoustikov, S. Sibley, M. E. Thompson, and S. R. Forrest, Nature (London) 395, 151 (1998).
- ⁴D. F. O'Brien, M. A. Baldo, M. E. Thompson, and S. R. Forrest, Appl. Phys. Lett. **74**, 442 (1999).
- ⁵ M. A. Baldo, S. Lamansky, P. E. Burrows, M. E. Thompson, and S. R. Forrest, Appl. Phys. Lett. **75**, 4 (1999).
- ⁶C. Adachi, M. A. Baldo, and S. R. Forrest, Appl. Phys. Lett. 77, 904 (2000).
- ⁷S. Lamansky, P. Djurovich, D. Murphy, F. Abdel-Razzaq, H.-E. Lee, C. Adachi, P. E. Burrows, S. R. Forrest, and M. E. Thompson, J. Am. Chem. Soc. (submitted).
- ⁸C. W. Tang, SID Digest **96**, 181 (1996).
- ⁹ Y. Hamada, H. Kanno, T. Tsujioka, H. Takahashi, and T. Usuki, Appl. Phys. Lett. **75**, 1682 (1999).
- ¹⁰ P. E. Burrows, S. R. Forrest, S. P. Sibley, and M. E. Thompson, Appl. Phys. Lett. **69**, 2959 (1996).
- ¹¹Y. Hamada, IEEE Trans. Electron Devices **44**, 1208 (1997).
- ¹²Y. Sakakibara, S. Okutsu, T. Enokida, and T. Tani, Appl. Phys. Lett. 74, 2587 (1999).
- ¹³ J. Kido, H. Hayase, K. Hongawa, K. Nagai, and K. Okamoto, Appl. Phys. Lett. **65**, 2124 (1994).
- ¹⁴C. Adachi, M. A. Baldo, and S. R. Forrest, J. Appl. Phys. 87, 8049 (2000).
- ¹⁵G. L. J. A. Rikken, Phys. Rev. A **51**, 4906 (1995).
- ¹⁶M. A. Baldo, M. E. Thompson, and S. R. Forrest, Nature (London) 403, 750 (2000).
- ¹⁷B. W. D'Andrade, M. A. Baldo, C. Adachi, M. E. Thompson, and S. R. Forrest (unpublished).
- ¹⁸ Y. T. Tao, E. Balasubramaniam, A. Danel, B. Jarosz, and P. Tomasik, Appl. Phys. Lett. 77, 1575 (2000).
- ¹⁹ M. A. Baldo, C. Adachi, and S. R. Forrest, Phys. Rev. B **62**, 10967 (2000).
- ²⁰ R. C. Kwong, S. Sibley, T. Dubovoy, M. A. Baldo, S. R. Forrest, and M. E. Thompson, Chem. Mater. 11, 3709 (1999).